

<b>Notice of References Cited</b>	Application/Control No. 10/660,561	Applicant(s)/Patent Under Reexamination LEE ET AL.	
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*		Document Number Country Code-Number-Kind Code	Date MM-YYYY	Name	Classification
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	C	US-6,596,377	07-2003	Hersee et al.	428/312.2
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	M	US-			

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**NON-PATENT DOCUMENTS**

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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.